

Qorvo QPD0005 GaN RF Transistors

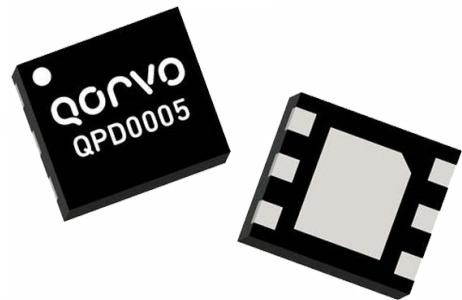
Product Overview

27/04/2021

For the most up-to-date information, visit www.mouser.com or the supplier's website.

Description

Qorvo QPD0005 GaN RF Transistors are single-path discrete GaN on SiC High-Electron-Mobility Transistors (HEMTs) in a plastic overmold DFN package. These RF transistors operate from 2.5GHz to 5GHz frequency range. The QPD0005 RF transistors are single-stage, unmatched transistors capable of delivering PSAT of 8.7W at 48V operation. These transistors come in 4.5mm x 4.0mm dimensions and are RoHS compliant. Applications include WCDMA / LTE, macrocell base station, microcell base station, small cell, active antenna, 5G massive MIMO, and general purpose applications.



Features

- Operate from 2.5GHz to 5GHz frequency range
- Single-stage, unmatched transistors capable of delivering PSAT of 8.7W at 48V operation
- 4.5mm x 4.0mm DFN package dimensions
- RoHS compliant

Specifications

- 48V operating drain voltage
- 72.9% maximum drain efficiency at 3.6GHz
- 18.8dB efficiency-tuned P3dB gain @ 3.6GHz

Associated Products

- [Qorvo GaN Transistor Solutions for Sub 6GHz 5G](#)
- [Qorvo QPD0007 GaN RF Transistors](#)
- [Qorvo QPD0010 GaN RF Transistors](#)

Associated Evaluation Board

- [Qorvo QPD0005 Evaluation Board](#)

Mouser Part Number(s)

[772-QPD0005TR13](#)

[772-QPD0005SR](#)

To learn more, visit <https://www.mouser.com/new/qorvo/qorvo-qpd0005-transistors/>